

IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of the Claim:

1. (Currently amended) A semiconductor device with ESD protection, comprising:

a guard ring;

a MOS transistor array formed in a region surrounded by said guard ring and comprising a first MOS transistor and a second MOS transistor, wherein ~~a channel length of said first MOS transistor is equal to that of said second MOS transistor, and~~ said first MOS transistor is closer to said guard ring than second MOS transistor is in a horizontal direction in which said first MOS transistor and said second MOS transistor are arranged alternatively;

a first resistor having one end electrically connected to a gate of said first MOS transistor and the other end grounded; and

a second resistor having one end electrically connected to a gate of said second MOS transistor and the other end grounded, wherein a resistance value of said first resistor is greater than that of said second resistor.

2. (Cancelled)